

CLAIMS

WHAT IS CLAIMED:

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1. A method, comprising:
defining a process task;
performing a process simulation function to produce simulation data corresponding to
said process task; and
interfacing said simulation data with a process control environment for controlling a
manufacturing process of a semiconductor device;

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2. The method described in claim 1, further comprising performing a
manufacturing process of the semiconductor device based upon said interfacing of said
simulation data with said process control environment.
3. The method described in claim 2, wherein performing manufacturing process
of said semiconductor device further comprises processing a semiconductor wafer.
4. The method described in claim 3, wherein defining a process task further
comprises defining a photolithography process task.
5. The method described in claim 3, wherein defining a process task further
comprises defining an etch process task.
6. The method described in claim 3, wherein defining a process task further
comprises defining a chemical-mechanical polishing process task.

7. The method described in claim 3, wherein defining a process task further comprises defining an implant process task.

8. The method described in claim 3, wherein defining a process task further comprises defining a diffusion process task.

9. The method described in claim 3, wherein performing a process simulation function further comprises:

preparing at least one processing model for simulation;

executing a simulation using said processing model to generate a simulation result;

determining whether said simulation result is within a predetermined specification;

and

applying said simulation result into at least one manufacturing parameter in response

to a determination that said simulation result is within said predetermined specification.

10. The method described in claim 9, further comprising modifying said model in response to a determination that said simulation result is not within said predetermined specification.

11. The method described in claim 9, wherein preparing at least one processing model for simulation further comprises:

defining at least one processing model;

validating said defined model;

acquiring data for operation of said defined model; and

populating said defined model with said acquired model.

12. The method described in claim 11, wherein defining at least one processing model further comprises defining at least one of a device physics model, a process model, and an equipment model.

13. The method described in claim 11, wherein validating said defined model further comprises integrating a plurality of defined models into a simulation environment.

14. The method described in claim 9, wherein executing said simulation using said processing model to generate a simulation result further comprises:
modulating at least one variability in said processing model;
executing a model behavior based upon said variability;
determining at least one component of variation based upon said execution of the model behavior; and
determining whether component of variation is within a predetermined specification.

15. The method described in claim 14, wherein modulating at least one variability in said processing model further comprises modulating a temperature component.

16. The method described in claim 14, further comprising performing a predictive state analysis in response to said execution of said model behavior.

17. The method described in claim 14, further comprising performing a sensitivity analysis in response to said execution of said model behavior.

18. The method described in claim 9, wherein applying said simulation result into at least one manufacturing parameter further comprises modifying at least one manufacturing control parameter based upon said simulation result.

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19. A system, comprising:

a computer system;

a manufacturing model coupled with said computer system, said manufacturing-model being capable of generating and modifying at least one control input parameter signal;

a machine interface coupled with said manufacturing model, said machine interface being capable of receiving process recipes from said manufacturing model;

a processing tool capable of processing semiconductor wafers and coupled with said machine interface, said first processing tool being capable of receiving at least one control input parameter signal from said machine interface;

a metrology tool coupled with said first processing tool and said second processing tool, said metrology tool being capable of acquiring metrology data;

a metrology data analysis unit coupled with said metrology, said metrology data analysis unit being capable of organizing said acquired metrology data; and

a simulation environment coupled to said metrology data analysis unit and said computer system, said simulation environment capable of producing simulation data for controlling manufacturing of semiconductor wafers.

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20. The system of claim 19, wherein said computer system is capable of generating modification data for modifying at least one control input parameter in response to a said simulation data.

5 21. The system of claim 20, wherein said manufacturing model is capable of modifying said control input parameter in response to said modification data.

22. The system of claim 19, wherein said simulation environment comprises:

a simulator, said simulator being capable of simulating a manufacturing process of a

semiconductor wafer;

a device physics model coupled to said simulator, said device physics model being capable of emulating semiconductor wafer manufacturing characteristics;

a process model coupled to said simulator, said process model being capable of emulating a semiconductor wafer manufacturing process;

an equipment model coupled to said simulator, said equipment model being capable of emulating a semiconductor wafer manufacturing process tool; and

a process control interface coupled to said simulator, said process control interface being capable of facilitating communication between said simulation environment and a process control environment.

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23. An apparatus, comprising:

means for defining a process task;

means for performing a process simulation function to produce simulation data corresponding to said process task; and

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defining a process task;

interfacing said simulation data with a process control environment for controlling a manufacturing process of a semiconductor device;

25. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 24, further comprising performing a manufacturing process of the semiconductor device based upon said interfacing of said simulation data with said process control environment.

26. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 25, wherein performing manufacturing process of said semiconductor device further comprises processing a semiconductor wafer.

27. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 26, wherein defining a process task comprises defining a photolithography process task.

28. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 26, wherein defining a process task comprises defining an etch process task.

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29. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 26, wherein defining a process task comprises defining a chemical-mechanical polishing process task.

30. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 26, wherein defining a process task further comprises defining an implant process task.

31. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 26, wherein defining a process task further comprises defining a diffusion polishing process task.

32. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 26, wherein

20 performing a process simulation function further comprises:

preparing at least one processing model for simulation;

executing a simulation using said processing model to generate a simulation result;

determining whether said simulation result is within a predetermined specification;

and

applying said simulation result into at least one manufacturing parameter in response to a determination that said simulation result is within said predetermined specification.

5 33. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 32, further comprising modifying said model in response to a determination that said simulation result is not within said predetermined specification.

10 34. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 32, wherein preparing at least one processing model for simulation further comprises:
15 defining at least one processing model;
 validating said defined model;
 acquiring data for operation of said defined model; and
 populating said defined model with said acquired model.

20 35. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 34, wherein defining at least one processing model comprises defining at least one of a device physics model, a process model, and an equipment model.

 36. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 34, wherein validating

37. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 32, wherein executing said simulation using said processing model to generate a simulation result further comprises:

executing a model behavior based upon said variability;

model behavior; and

38. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 37, wherein the method of generating at least one variability in said processing model further comprises modulating a temperature component.

40. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 37, further comprising instructions that cause the computer to perform the steps of:
 (a) receiving a sensitivity analysis in response to said execution of said model behavior

41. The computer readable program storage device encoded with instructions that, when executed by a computer, performs the method described in claim 32, wherein applying said simulation result into at least one manufacturing parameter further comprises modifying at least one manufacturing control parameter based upon said simulation result.

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42. A method, comprising:

defining a process task;

performing a process simulation function to produce simulation data corresponding to

said process task, said process simulation function comprising:

preparing at least one processing model for simulation;

executing a simulation using said processing model to generate a simulation result;

determining whether said simulation result is within a predetermined specification; and

applying said simulation result into at least one manufacturing parameter in response to a determination that said simulation result is within said predetermined specification.

and

interfacing said simulation data with a process control environment for controlling a

manufacturing process of a semiconductor device;

43. The method described in claim 38, further comprising modifying said model in response to a determination that said simulation result is not within said predetermined specification.

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44. The method described in claim 38, wherein preparing at least one processing model for simulation further comprises:

defining at least one processing model;

validating said defined model;

5 acquiring data for operation of said defined model; and

populating said defined model with said acquired model.

45. The method described in claim 40, wherein defining at least one processing model further comprises defining at least one of a device physics model, a process model, and an equipment model.

46. The method described in claim 40, wherein validating said defined model further comprises integrating a plurality of defined models into a simulation environment.

47. The method described in claim 38, wherein executing said simulation using said processing model to generate a simulation result further comprises:

modulating at least one variability in said processing model;

executing a model behavior based upon said variability;

determining at least one component of variation based upon said execution of the model behavior; and

determining whether component of variation is within a predetermined specification.

48. A method, comprising:

defining a graph relating to a desired results of a processed semiconductor wafer;

25 defining a graph relating to a predicted results of said processed semiconductor wafer;

comparing said graph relating to said desired results to said graph relating to said predicted results to determine a difference between said graphs; and adjusting at least one control input parameter for a manufacturing process based upon said difference between said graphs.

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49. The method described in claim 48, wherein defining said graph relating to the desired results of said processed semiconductor wafer further comprises defining said graph relating to at least one electrical parameter of a semiconductor wafer.

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50. The method described in claim 49, wherein defining said graph relating to at least one electrical parameter of a semiconductor wafer further comprises defining said graph relating to a speed of operation of a circuit formed on said semiconductor wafer.

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51. The method described in claim 48, wherein defining said graph relating to the predicted results of said processed semiconductor wafer further comprises defining said graph relating to at least one electrical parameter of a semiconductor wafer.

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52. The method described in claim 51, wherein defining said graph relating to at least one electrical parameter of a semiconductor wafer further comprises defining said graph relating to a speed of operation of a circuit formed on said semiconductor wafer.

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53. The method described in claim 48, further comprising:
defining a graph relating to an actual result of said processed semiconductor wafer;
comparing said graph relating to said actual result to said graph relating to said desired results and to said graph relating to said predicted results;

adjusting at least one control input parameter for a manufacturing process based upon said comparison.

54. The method described in claim 53, wherein defining said graph relating to the
5 actual results of said processed semiconductor wafer further comprises defining said graph
relating to at least one electrical parameter of a semiconductor wafer.

55. The method described in claim 55, wherein defining said graph relating to at least one electrical parameter of a semiconductor wafer further comprises defining said graph relating to a speed of operation of a circuit formed on said semiconductor wafer.

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